ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor device that comprises the steps of providing a semiconductor wafer including a patterned layer, forming a first insulating layer over the patterned layer of the semiconductor wafer, the first insulating layer including a first index of refraction, forming a second insulating layer over the first insulating layer, the second insulating layer including a second index of refraction smaller than the first index of refraction, removing the second insulating layer by a planarizing process, and detecting a change in index of refraction during the planarizing process.

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